

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-20. (Canceled)

21. (Currently Amended) A method for fabricating a semiconductor device, comprising the steps of:

forming, on an underlying wiring, a barrier metal film of a metal ~~whose conductivity will not be lost when~~ that retains its conductivity even after the metal is oxidized;

forming a seed layer in contact with the barrier metal film; and

forming a conductive film as an upper-layer wiring, such that conductive film is in contact with the seed layer.

22. (Currently Amended) The method of Claim 21, wherein the metal ~~whose conductivity will not be lost when~~ that retains its conductivity even after the metal is oxidized is Ru, Ir or an alloy containing Ru or Ir.

23. (Canceled)

24. (Previously Presented) The method of Claim 21, wherein the seed layer is composed of copper or a copper alloy.

Claims 25-31. (Canceled)

32. (Previously Presented) The method of Claim 21 further comprising the step of, after forming the conductive film, forming the upper-layer wiring by etching the conductive film using a mask pattern covering a wiring forming region.

33. (Previously Presented) The method of Claim 21, wherein the barrier metal film includes a conductive metal oxide.

34. (Previously Presented) The method of Claim 21, wherein in the step of forming the conductive film, the barrier metal film is oxidized to form a metal oxide film

35. (Previously Presented) A method for fabricating a semiconductor device comprising the steps of :

forming, on an underlying wiring, a barrier metal film composed of a conductive metal oxide;

forming a seed layer in contact with the barrier metal film, and

forming a conductive film as an upper-layer wiring, such that the conductive film is in contact with the seed layer,

wherein the seed layer is composed of the same metal as the conductive film.

36. (Previously Presented) The method of Claim 35, wherein the conductive metal oxide is  $\text{RuO}_2$ ,  $\text{IrO}_2$  or an alloy oxide containing Ru or Ir.

37. (Previously Presented) The method of Claim 35, wherein the seed layer is composed of copper or a copper alloy.

38. (Previously Presented) The method of Claim 35 further comprising the step of, after forming the conductive film, forming the upper-layer wiring by etching the conductive film using a mask pattern covering a wiring forming region.